




# Power MOSFETS


## DATASHEET

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**LM60026NAK8A**

N-Channel  
Enhancement Mode MOSFET

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Quality Management Systems

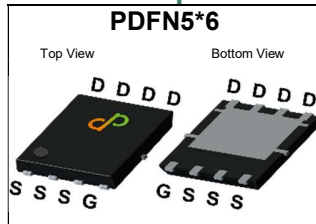
ISO 9001:2015 Certificate

# LM60026NAK8A

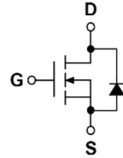


## N-Channel Enhancement Mode MOSFET

### Pin Description



### Symbol



### Product Summary

Symbol	N-Channel	Unit
$V_{DSS}$	60	V
$R_{DS(ON)-Max}$	2.6	m $\Omega$
$I_D$	142	A

### Feature

- Optimized high performance of  $R_{on}$  and  $Q_g$
- Reliable and Rugged
- ROHS Compliant & Halogen-Free
- 100% UIS and  $R_g$  Tested

### Applications

- DC-DC Converter
- Load Switching

### Ordering Information

Orderable Part Number	Package Type	Form	Shipping	Marking
LM60026NAK8A	PDFN5*6	Tape & Reel	5000 / Tape & Reel	60026 □□□□□□

Note : □□□□□□ = Lot Code

### Absolute Maximum Ratings (T<sub>J</sub>=25°C Unless Otherwise Noted)

Symbol	Parameter	N-Channel	Unit	
$V_{DSS}$	Drain-Source Voltage	60	V	
$V_{GSS}$	Gate-Source Voltage	±20		
$T_J$	Maximum Junction Temperature	150	°C	
$T_{STG}$	Storage Temperature Range	-55 to 150	°C	
$I_S$	Diode Continuous Forward Current	$T_C=25^\circ C$	87	A
$I_{DM}$	Pulse Drain Current Tested	$T_C=25^\circ C$	400	A
$I_D$	Continuous Drain Current	$T_C=25^\circ C$	142 <sup>①</sup>	A
		$T_C=100^\circ C$	121	
$P_D$	Maximum Power Dissipation	$T_C=25^\circ C$	96	W
		$T_C=100^\circ C$	39	
$I_D$	Continuous Drain Current	$T_A=25^\circ C$	30.8	A
		$T_A=70^\circ C$	24.6	
$P_D$	Maximum Power Dissipation	$T_A=25^\circ C$	2.5	W
		$T_A=70^\circ C$	1.6	
$I_{AS}^{②}$	Avalanche Current, Single pulse	L=0.1mH	30	A
		L=0.5mH	15	
$E_{AS}^{②}$	Avalanche Energy, Single pulse	L=0.1mH	45	mJ
		L=0.5mH	56	

### Thermal Characteristics

Symbol	Parameter	Rating	Unit	
$R_{\theta JC}$	Thermal Resistance-Junction to Case	Steady State	1.3	°C/W
$R_{\theta JA}^{③}$	Thermal Resistance-Junction to Ambient	Steady State	50	°C/W

Note ① : Max. current is limited by bonding wire

Note ② : UIS tested and pulse width are limited by maximum junction temperature 150°C

Note ③ : Surface Mounted on 1in<sup>2</sup> FR-4 board with 1oz.

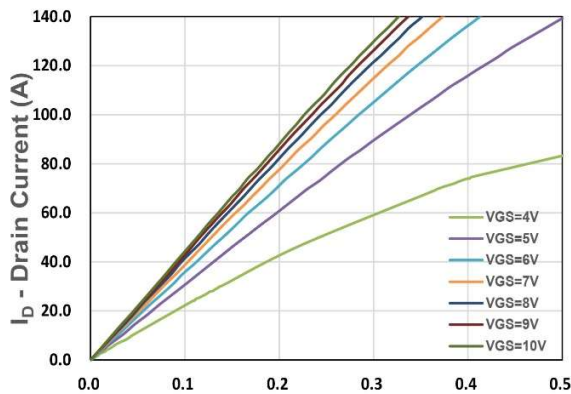
## N-Channel Electrical Characteristics (T<sub>J</sub>=25°C Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static Electrical Characteristics</b>						
<b>BV<sub>DSS</sub></b>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>DS</sub> =250uA	60	-	-	V
<b>I<sub>DSS</sub></b>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =48V, V <sub>GS</sub> =0V	-	-	1	uA
<b>V<sub>GS(th)</sub></b>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>DS</sub> =250uA	1	2	3	V
<b>I<sub>GSS</sub></b>	Gate Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA
<b>R<sub>DS(ON)</sub></b> <sup>④</sup>	Drain-Source On-state Resistance	V <sub>GS</sub> =10V, I <sub>DS</sub> =20A	-	2.2	2.6	mΩ
		V <sub>GS</sub> =4.5V, I <sub>DS</sub> =10A	-	3.5	4.5	
<b>gfs</b>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>DS</sub> =20A	-	50	-	S
<b>Dynamic Characteristics</b> <sup>⑤</sup>						
<b>R<sub>G</sub></b>	Gate Resistance	V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, Freq.=1MHz	-	1.7	-	Ω
<b>C<sub>iss</sub></b>	Input Capacitance	V <sub>GS</sub> =0V, V <sub>DS</sub> =30V, Freq.=1MHz	-	4635	-	pF
<b>C<sub>oss</sub></b>	Output Capacitance		-	1714	-	
<b>C<sub>rss</sub></b>	Reverse Transfer Capacitance		-	80	-	
<b>td(ON)</b>	Turn-on Delay Time	V <sub>GS</sub> =10V, V <sub>DS</sub> =30V, I <sub>D</sub> =1A, R <sub>GEN</sub> =6Ω	-	13.8	-	nS
<b>t<sub>r</sub></b>	Turn-on Rise Time		-	35	-	
<b>t<sub>d(OFF)</sub></b>	Turn-off Delay Time		-	70	-	
<b>t<sub>f</sub></b>	Turn-off Fall Time		-	45	-	
<b>Q<sub>g</sub></b>	Total Gate Charge	V <sub>GS</sub> =4.5V, V <sub>DS</sub> =30V, I <sub>D</sub> =20A	-	39.5	-	nC
<b>Q<sub>g</sub></b>	Total Gate Charge	V <sub>GS</sub> =10V, V <sub>DS</sub> =15V, I <sub>D</sub> =20A	-	76.2	-	
<b>Q<sub>gs</sub></b>	Gate-Source Charge		-	13.4	-	
<b>Q<sub>gd</sub></b>	Gate-Drain Charge		-	17.5	-	
<b>Source-Drain Characteristics</b>						
<b>V<sub>SD</sub></b> <sup>④</sup>	Diode Forward Voltage	I <sub>SD</sub> =20A, V <sub>GS</sub> =0V	-	0.8	1.1	V
<b>t<sub>rr</sub></b>	Reverse Recovery Time	I <sub>F</sub> =20A, V <sub>R</sub> =30V	-	27.6	-	nS
<b>Q<sub>rr</sub></b>	Reverse Recovery Charge	dI <sub>F</sub> /dt=100A/μs	-	20.8	-	nC

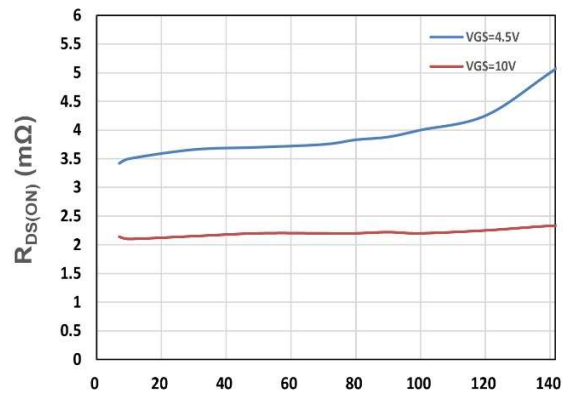
Note ④ : Pulse test (pulse width≤300us, duty cycle≤2%).

Note ⑤ : Guaranteed by design, not subject to production testing.

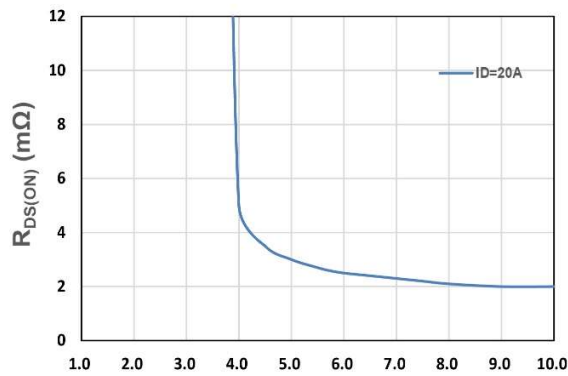
## N-Channel Typical Characteristics



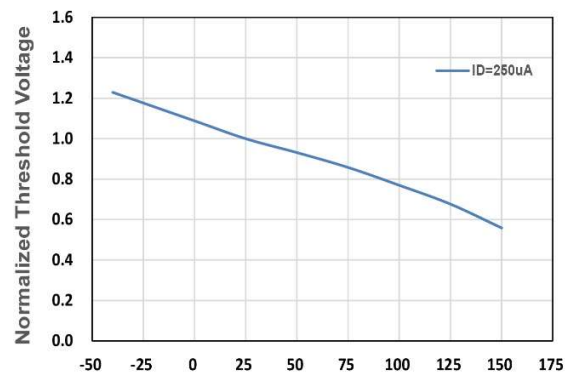
$V_{DS}$  - Drain - Source Voltage (V)  
Figure 1. Output Characteristics



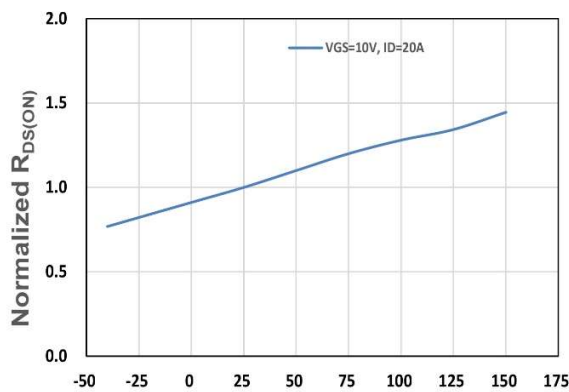
$I_D$  - Drain Current (A)  
Figure 2. On-Resistance vs.  $I_D$



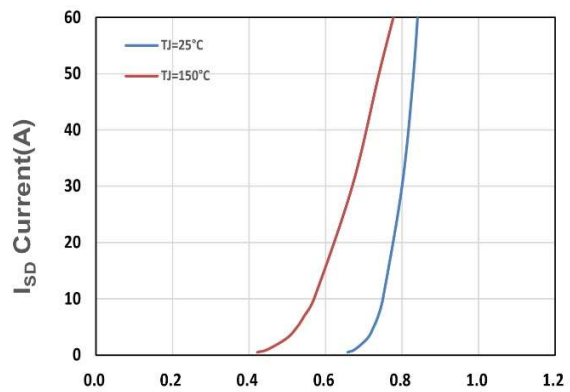
$V_{GS}$  - Gate - Source Voltage (V)  
Figure 3. On-Resistance vs.  $V_{GS}$



$T_j$ , Junction Temperature( $^{\circ}C$ )  
Figure 4. Gate Threshold Voltage



$T_j$ , Junction Temperature( $^{\circ}C$ )  
Figure 5. Drain-Source On Resistance



$V_{SD}$ , Source-Drain Voltage(V)  
Figure 6. Source-Drain Diode Forward

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